Elektronische Bauelemente

2SC2383

1A , 160V

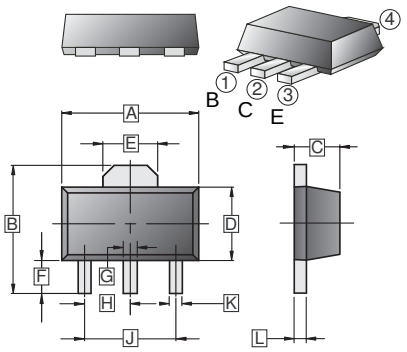
NPN Plastic Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Small Flat Package
- General Purpose Application

SOT-89

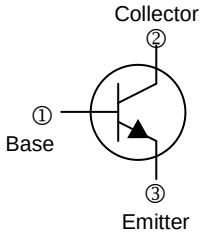


CLASSIFICATION OF h_{FE}

Product-Rank	2SC2383-O	2SC2383-Y
Range	100~200	160~320

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-89	1K	7 inch



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.60	G	0.40	0.58
B	3.94	4.25	H	1.50 TYP	
C	1.40	1.60	J	3.00 TYP	
D	2.25	2.60	K	0.32	0.52
E	1.50	1.85	L	0.35	0.44
F	0.89	1.20			

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector-Base Voltage	V_{CBO}	160	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current-Continuous	I_C	1	A
Collector Power Dissipation	P_C	0.5	mW
Junction & Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	160	-	-	V	I_C=0.1mA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160	-	-	V	I_C=10mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	-	-	V	I_E=10μA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	1	μA	V_{CB}=150V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	1	μA	V_{EB}=6V, I_C=0
DC Current Gain	h_{FE}	100	-	320		V_{CE}=5V, I_C=200mA
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	-	-	1	V	I_C=500mA, I_B=50mA
Base-Emitter voltage	V_{BE}	0.45	-	0.75	V	I_C=5mA, V_{CE}=5V
Transition Frequency	f_T	20	-	-	MHz	V_{CE}=5V,I_C=200mA
Collector Output Capacitance	C_{OB}	-	-	20	pF	V_{CB}=10V, I_E=0, f=1MHz